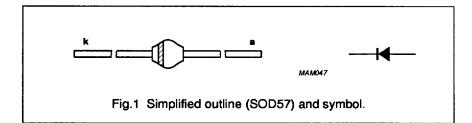
**BYV96** series

#### **FEATURES**

- · Glass passivated
- High maximum operating temperature
- Low leakage current
- · Excellent stability
- Guaranteed avalanche energy absorption capability
- Available in ammo-pack.

#### **DESCRIPTION**

Rugged glass package, using a high temperature alloyed construction. This package is hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched.



#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>RRM</sub>	repetitive peak reverse voltage				
	BYV96D		_	800	v
	BYV96E		-	1000	v
V <sub>R</sub>	continuous reverse voltage				
	BYV96D		-	800	v
	BYV96E		_	1000	v
I <sub>F(AV)</sub>	average forward current	T <sub>tp</sub> = 55 °C; lead length = 10 mm see Fig 2; averaged over any 20 ms period; see also Fig 6	-	1.5	Α
		T <sub>amb</sub> = 55 °C; PCB mounting (see Fig.11); see Fig 3; averaged over any 20 ms period; see also Fig 6	-	0.8	A
I <sub>FRM</sub>	repetitive peak forward current	T <sub>tp</sub> = 55 °C; see Fig 4	_	17	Α
		T <sub>amb</sub> = 55 °C; see Fig 5	_	9	Α
I <sub>FSM</sub>	non-repetitive peak forward current	t = 10 ms half sine wave; T <sub>j</sub> = T <sub>j max</sub> prior to surge; V <sub>R</sub> = V <sub>RRMmax</sub>	_	35	Α
E <sub>RSM</sub>	non-repetitive peak reverse avalanche energy	L = 120 mH; $T_j = T_{j \text{ max}}$ prior to surge; inductive load switched off	_	10	mJ
T <sub>stg</sub>	storage temperature		-65	+175	°C
Tj	junction temperature	see Fig 7	-65	+175	°C

Philips Semiconductors Product specification

# Fast soft-recovery controlled avalanche rectifiers

BYV96 series

#### **ELECTRICAL CHARACTERISTICS**

 $T_i = 25$  °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>F</sub>	forward voltage	$I_F = 3 A$ ; $T_j = T_{j \text{ max}}$ ; see Fig 8	_	-	1.35	V
		I <sub>F</sub> = 3 A; see Fig 8	-	-	1.60	V
V <sub>(BR)R</sub>	reverse avalanche breakdown voltage	i <sub>R</sub> = 0.1 mA				
	BYV96D		900	_	_	V
	BYV96E		1100	-	-	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = V <sub>RRMmax</sub> ; see Fig 9	_	_	1	μА
		V <sub>R</sub> = V <sub>RRMmax</sub> ; T <sub>j</sub> = 165 °C; see Fig 9	_	_	150	μА
t <sub>rr</sub>	reverse recovery time	when switched from $I_F = 0.5$ A to $I_R = 1$ A; measured at $I_R = 0.25$ A; see Fig 12	-	-	300	ns
C <sub>d</sub>	diode capacitance	f = 1 MHz; V <sub>R</sub> = 0 V; see Fig 10	-	40	-	pF
dI <sub>R</sub>	maximum slope of reverse recovery current	when switched from $I_F = 1$ A to $V_R \ge 30$ V and $dI_F/dt = -1$ A/ $\mu$ s; see Fig.13	-	-	6	A/μs

### THERMAL CHARACTERISTICS

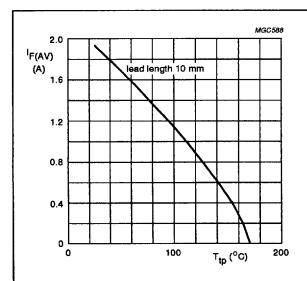
SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-tp</sub>	thermal resistance from junction to tie-point	lead length = 10 mm	46	K/W
R <sub>th i-a</sub>	thermal resistance from junction to ambient	note 1	100	K/W

### Note

1. Device mounted on an epoxy-glass printed-circuit board, 1.5 mm thick; thickness of Cu-layer ≥40 μm, see Fig.11. For more information please refer to the *'General Part of Handbook SC01'* 

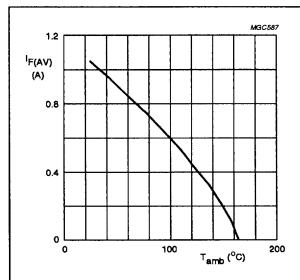
BYV96 series

#### **GRAPHICAL DATA**



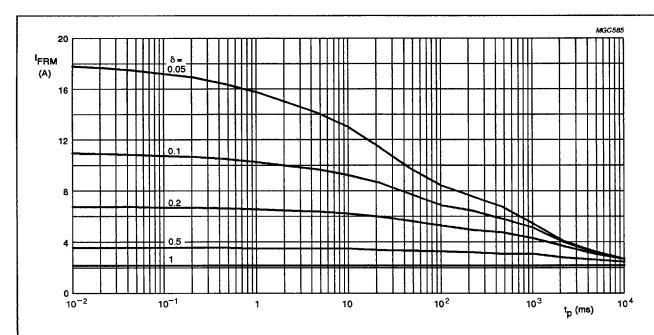
a = 1.57;  $V_R = V_{RRMmax}$ ;  $\delta = 0.5$ .

Fig.2 Maximum permissible average forward current as a function of tie-point temperature (including losses due to reverse leakage).



a = 1.57;  $V_R = V_{RRMmax}$ ;  $\delta$  = 0.5. Device mounted as shown in Fig.11.

Fig.3 Maximum permissible average forward current as a function of ambient temperature (including losses due to reverse leakage).

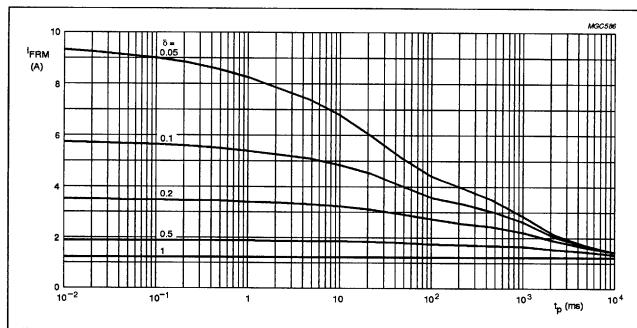


 $T_{tp} = 55$ °C;  $R_{th j-tp} = 46$  K/W.

 $V_{RRMmax}$  during 1 –  $\delta$ ; curves include derating for  $T_{j\,max}$  at  $V_{RRM}$  = 1000 V.

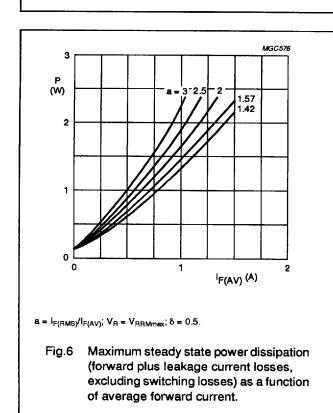
Fig.4 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.

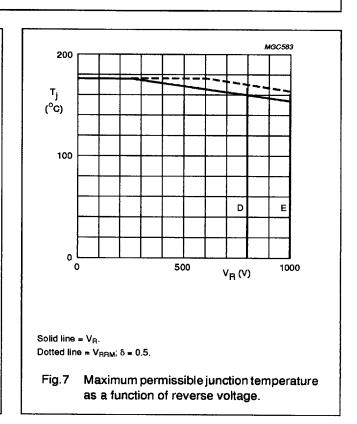
BYV96 series



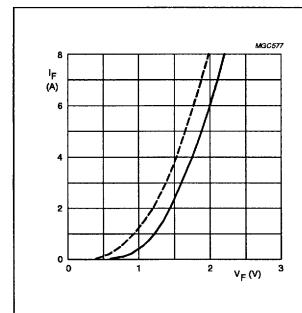
 $T_{amb}$  = 55 °C;  $R_{th,j-a}$  = 100 K/W.  $V_{RRMmex}$  during 1 –  $\delta$ ; curves include denating for  $T_{j,mex}$  at  $V_{RRM}$  = 1000 V.

Fig.5 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.



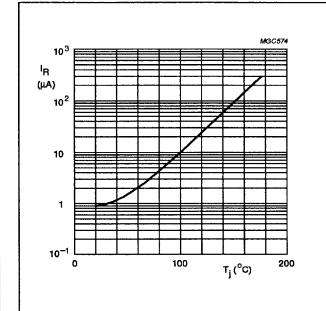


BYV96 series



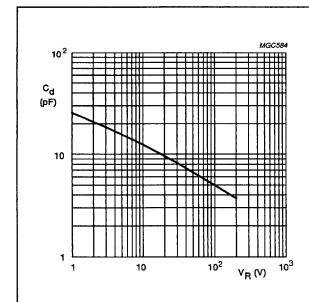
Dotted line:  $T_j = 175$  °C. Solid line:  $T_j = 25$  °C.

Fig.8 Forward current as a function of forward voltage; maximum values.



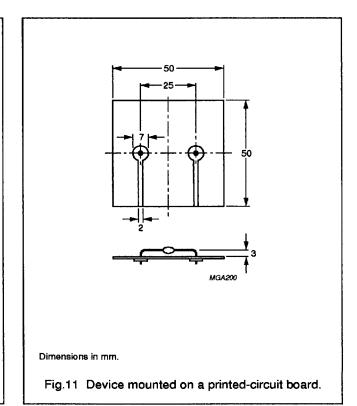
V<sub>R</sub> = V<sub>RRMmax</sub>.

Fig.9 Reverse current as a function of junction temperature; maximum values.

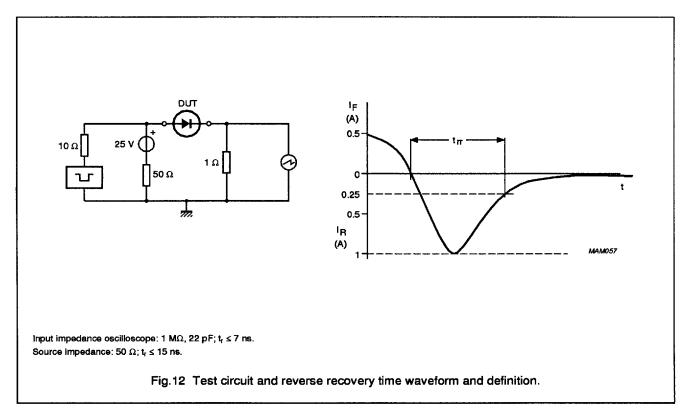


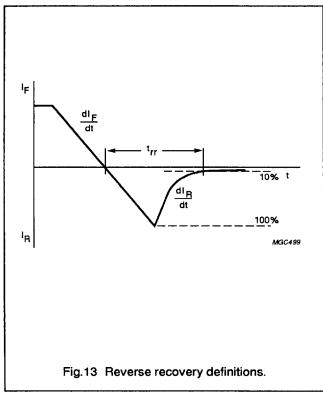
f = 1 MHz; T<sub>j</sub> = 25 °C.

Fig. 10 Diode capacitance as a function of reverse voltage; typical values.



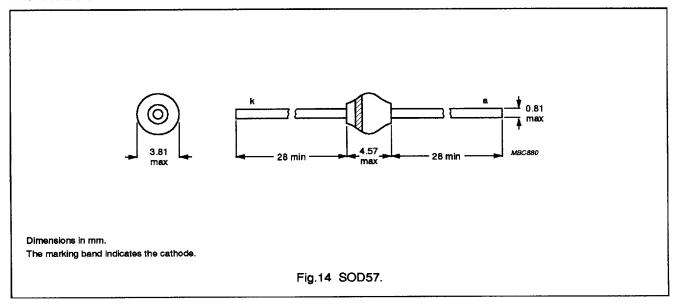
BYV96 series





BYV96 series

#### **PACKAGE OUTLINE**



#### **DEFINITIONS**

Data Sheet Status		
Objective specification	This data sheet contains target or goal specifications for product development.	
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later	
Product specification	This data sheet contains final product specifications.	
Limiting values		
more of the limiting values of the device at these or at	accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or may cause permanent damage to the device. These are stress ratings only and operation any other conditions above those given in the Characteristics sections of the specification limiting values for extended periods may affect device reliability.	
Application information		
Where application informat	ion is given, it is advisory and does not form part of the specification.	

#### **LIFE SUPPORT APPLICATIONS**

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.